

# **2021 28th International Workshop on Active-Matrix Flatpanel Displays and Devices (AM-FPD 2021)**

**Virtual Conference  
29 June – 2 July 2021**



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# PROGRAM

Date: Tuesday, June 29

## Opening Session (13 : 00~13 : 15)

### Welcome Address

H. Hamada, *Kinki Univ., Japan*

### Award Presentation

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<sup>1)</sup> *Osaka Prefecture Univ., JAPAN*

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<sup>1)</sup> *Global Zero Emission Res. Ctr., Nat'l Inst. of Advanced Industrial Sci. and Technol.(AIST), JAPAN*

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<sup>1)</sup> *Tokyo Univ. of Agriculture and Technol., JAPAN*, <sup>2)</sup> *Techno Research., Ltd., JAPAN*, <sup>3)</sup> *ORC MANUFACTURING Co., Ltd., JAPAN*

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<sup>1)</sup> *Ritsumeikan Univ., JAPAN*

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<sup>1</sup> *Sci. & Technol. Res. Labs.(STRL), Japan Broadcasting Corp.(NHK), JAPAN,* <sup>2</sup> *Tohoku Univ., JAPAN*
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<sup>1</sup> *Kyocera Corp., JAPAN,* <sup>2</sup> *OSRAM Opto Semiconductors GmbH, GERMANY*
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<sup>1)</sup> Princeton Univ., USA

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<sup>1)</sup> *NISSIN ION EQUIPMENT CO., LTD., JAPAN*, <sup>2)</sup> *NISSIN ELECTRIC CO., LTD., JAPAN*

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<sup>1)</sup> Ryukoku Univ., JAPAN

**Closing Remarks** (15 : 30~15 : 40)